

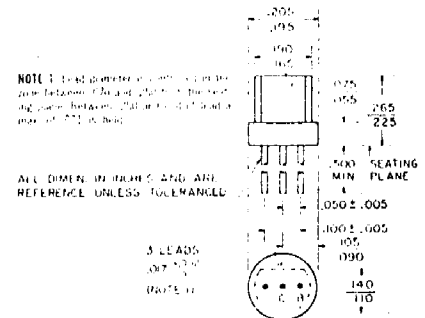
2N3855A,

Silicon
Transistor

absolute maximum ratings: (25°C) (unless otherwise specified)

Voltages			
Collector to Emitter	V_{CEO}	30	vols
Emitter to Base	V_{EB0}	4	vols
Collector to Base	V_{CB0}	30	vols
Current			
Collector (Steady State) †	I_C	100	mA
Dissipation			
Total Power (Free air at 25°C) ‡	P_T	200	mW
Total Power (Free air at 55°C) ‡	P_T	120	mW
Temperature			
Storage	T_S	-30 to 150°C	
Operating	T_J	100°C	
Lead soldering, $\frac{1}{16} \pm \frac{1}{32}$ " from case for 10 sec. max.	T_L	260°C	

†Determined from power limitations due to saturation voltage at this point.
‡Derate 2.67 mW/°C increase in ambient temperature above 25°C.



electrical characteristics: (25°C) (unless otherwise specified)

Static Characteristics

		Min.	Typ.	Max.	Units
Collector Cutoff Current ($V_{CE} = 18V$) ($V_{BE} = 18V, T_A = 100^\circ C$)	I_{CBO}			0.5	μA
	I_{EBO}			15	μA
Forward Current Transfer Ratio ($V_{CE} = 4.5V, I_C = 2mA$)	h_{FE}	60		120	
Emitter-Base Breakdown Voltage ($I_E = 500\mu A$)	BV_{EBO}	4			vols
Collector-Base Breakdown Voltage ($I_C = 1mA$)	BV_{CBO}	30	70		vols
Collector-Base Breakdown Voltage ($I_C = 0.1mA$)	BV_{CBO}	30			vols
Collector Saturation Voltage ($I_C = 10mA, I_B = 1mA$)	$V_{CE(SAT)}$			0.200	vols

Dynamic Characteristics

Gain Bandwidth Product ($V_{CE} = 10V, I_C = 5mA$)	f_T	130		450	MHz
Collector-Base Time Constant ($V_{CE} = 10V, I_C = 5mA$)	$r_b' C_c$		35	90	psec.
Output Capacitance ($V_{CE} = 10V, I_E = 0, f = 1MHz$)	C_{ob}			3.5	pF
Input Capacitance ($V_{BE} = 0.5V, I_E = 0, f = 1MHz$)	C_{ib}		16		pF
Case Capacitance			0.66		pF

